

**FX208**

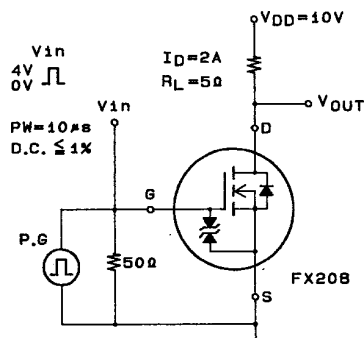
N-Channel Silicon MOSFET

Very High-Speed Switching Applications

Features

- Low ON-resistance.
- Very high-speed switching.
- 2.5V drive.

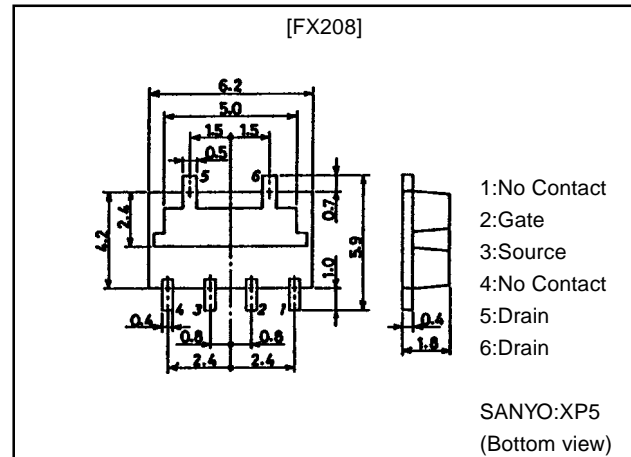
Switching Time Test Circuit



Package Dimensions

unit:mm

2121



Specifications

Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V_{DSS}		20	V
Gate-to-Source Voltage	V_{GSS}		±10	V
Drain Current (DC)	I_D		4	A
Drain Current (Pulse)	I_{DP}	$PW \leq 10\mu s$, duty cycle $\leq 1\%$	16	A
Allowable Power Dissipation	P_D	$T_c = 25^\circ C$	8	W
	P_D	Mounted on ceramic board (750mm ² × 0.8mm)	2	W
Channel Temperature	T_{ch}		150	°C
Storage Temperature	T_{stg}		-55 to +150	°C

Electrical Characteristics at Ta = 25°C

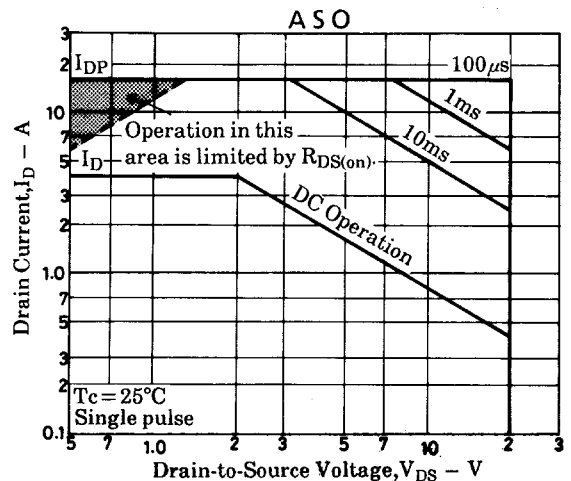
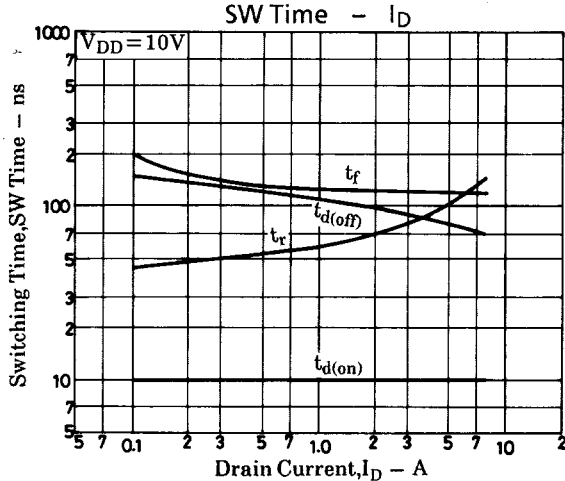
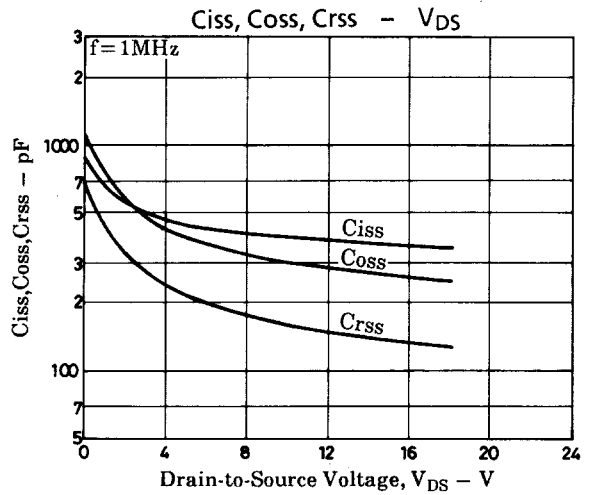
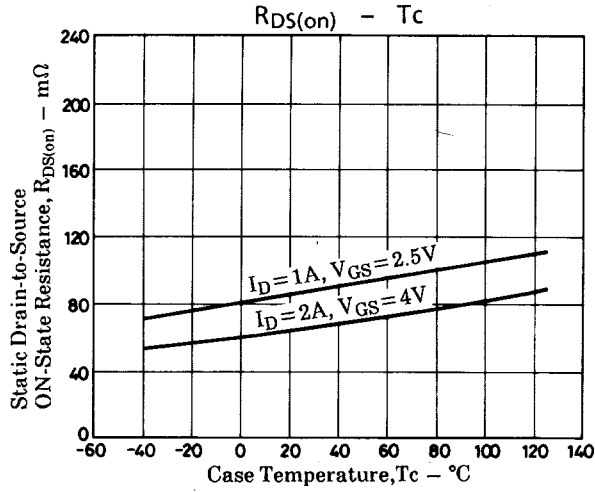
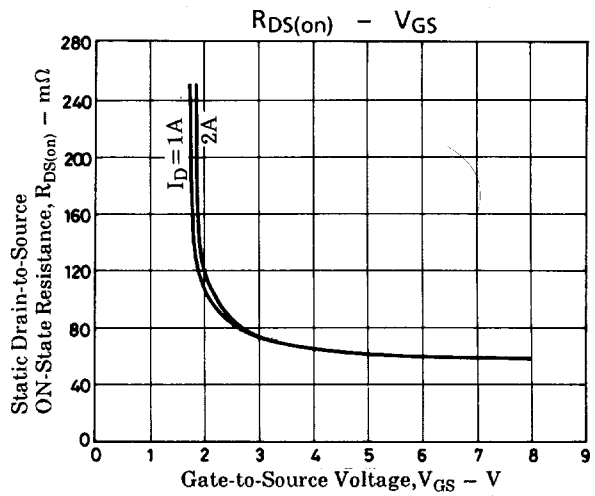
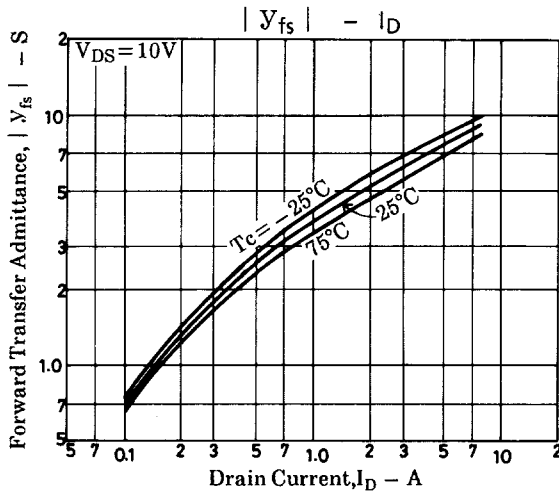
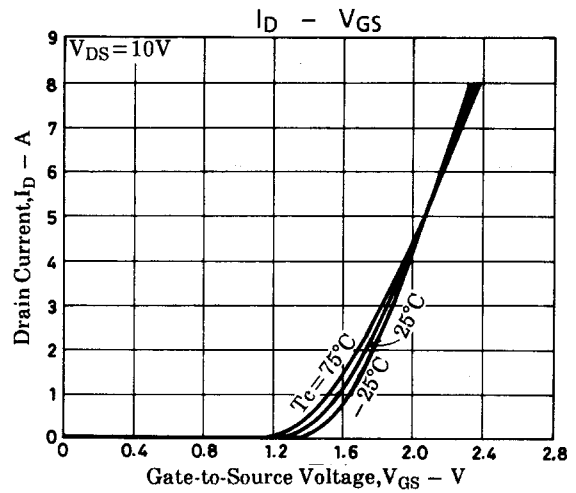
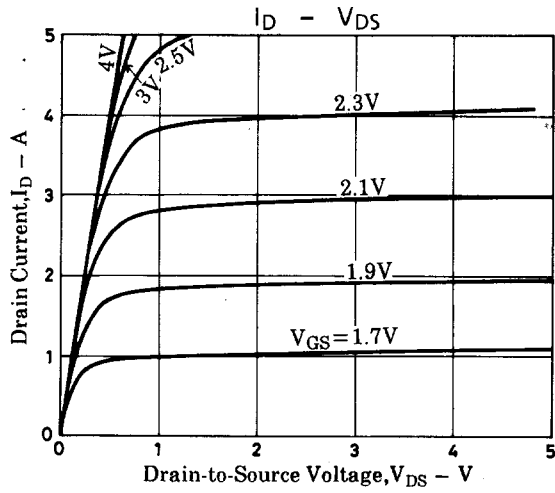
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
D-S Breakdown Voltage	$V_{(BR)DSS}$	$I_D = -1mA$, $V_{GS} = 0$	20			V
Zero-Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 16V$, $V_{GS} = 0$			100	µA
Gate-to-Source Leakage Current	I_{GSS}	$V_{GS} = \pm 8V$, $V_{DS} = 0$			±10	µA
Cutoff Voltage	$V_{GS(off)}$	$V_{DS} = 10V$, $I_D = 1mA$	0.5		1.5	V
Forward Transfer Admittance	$ Y_{fs} $	$V_{DS} = 10V$, $I_D = 2A$	3.5	5		S
Static Drain-to-Source ON-State Resistance	$R_{DS(on)}$	$I_D = 2A$, $V_{GS} = 4V$		65	85	mΩ
	$R_{DS(on)}$	$I_D = 1A$, $V_{GS} = 2.5V$		85	125	mΩ
Input Capacitance	C_{iss}	$V_{DS} = 10V$, $f = 1MHz$		400		pF
Output Capacitance	C_{oss}	$V_{DS} = 10V$, $f = 1MHz$		300		pF
Reverse Transfer Capacitance	C_{rss}	$V_{DS} = 10V$, $f = 1MHz$		160		pF
Turn-ON Delay Time	$t_{d(on)}$	See specified Test Circuit		20		ns
Rise Time	t_r	See specified Test Circuit		70		ns
Turn-OFF Delay Time	$t_{d(off)}$	See specified Test Circuit		100		ns
Fall Time	t_f	See specified Test Circuit		120		ns
Diode Forward Voltage	V_{SD}	$I_S = 4A$, $V_{GS} = 0$		1.0	1.2	V

· Marking:208

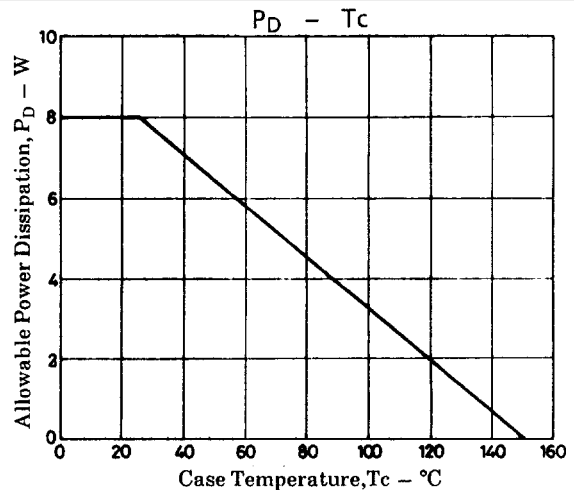
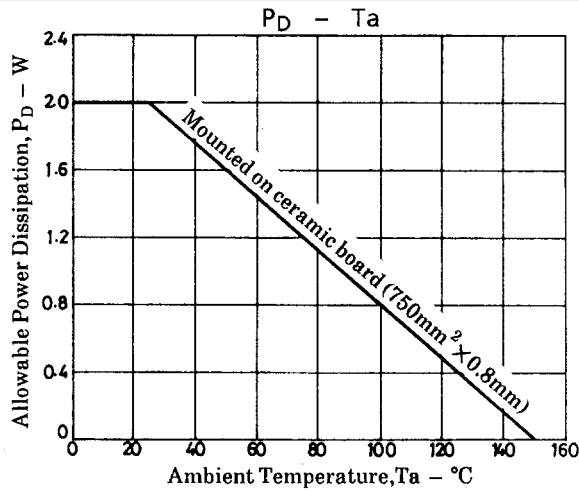
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